P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 60	0.020 at V_{GS} = - 10 V	- 50
	0.025 at V_{GS} = - 4.5 V	- 45

FEATURES

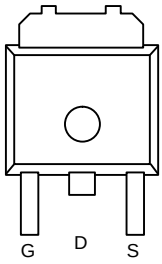
- TrenchFET® Power MOSFET
- Material categorization:

RoHS COMPLIANT
HALOGEN FREE

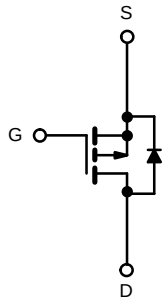
APPLICATIONS

- Load Switch

TO-252



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	- 50	A
	T_C = 125 °C		- 40	
Pulsed Drain Current		I_{DM}	- 160	
Avalanche Current		I_{AS}	- 50	
Single Pulse Avalanche Energy[a]	L = 0.1 mH	E_{AS}	125	mJ
Power Dissipation	T_C = 25 °C	P_D	113[c]	W
	T_A = 25 °C		2.5[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Junction-to-Ambient[b]	t ≤ 10 s	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Junction-to-Case		R_{thJC}	0.82	1.1	

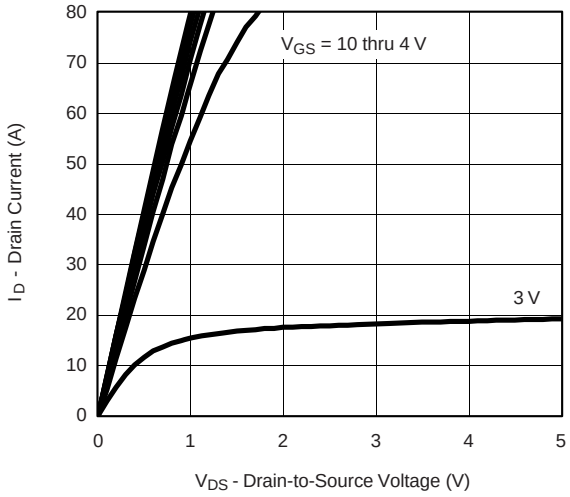
Notes:
a. Duty cycle ≤ 1 %.
b. When mounted on 1" square PCB (FR-4 material).
c. See SOA curve for voltage derating.
d. Package limited.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 1.5		- 3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 60 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 60 V, V_{GS} = 0 V, T_J = 125 °C			- 50	
		V_{DS} = - 60 V, V_{GS} = 0 V, T_J = 150 °C			- 100	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = - 5 V, V_{GS} = - 10 V	- 50			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 17 A		0.020	0.025	Ω
		V_{GS} = - 10 V, I_D = - 40 A, T_J = 125 °C			0.030	
		V_{GS} = - 10 V, I_D = - 40 A, T_J = 150 °C			0.035	
		V_{GS} = - 4.5 V, I_D = - 14 A		0.025	0.040	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 17 A		61		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 25 V, f = 1 MHz		2950		pF
Output Capacitance	C_{oss}			380		
Reverse Transfer Capacitance	C_{rss}			305		
Total Gate Charge[c]	Q_g	V_{DS} = - 30 V, V_{GS} = - 10 V, I_D = - 40 A		110	165	nC
Gate-Source Charge[c]	Q_{gs}			19		
Gate-Drain Charge[c]	Q_{gd}			28		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 30 V, R_L = 0.6 Ω, $I_D \cong$ - 40 A, V_{GEN} = - 10 V, R_G = 6 Ω		15	23	ns
Rise Time[c]	t_r			70	105	
Turn-Off Delay Time[c]	$t_{d(off)}$			175	260	
Fall Time[c]	t_f			175	260	
Source-Drain Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				- 40	A
Pulsed Current	I_{SM}				- 80	
Forward Voltage[a]	V_{SD}	I_F = - 40 A, V_{GS} = 0 V		- 1	- 1.6	V
Reverse Recovery Time	t_{rr}	I_F = - 40 A, dI/dt = 100 A/µs		45	70	ns

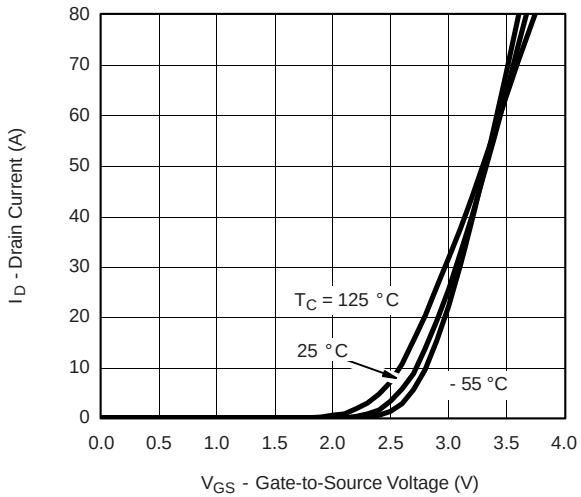
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

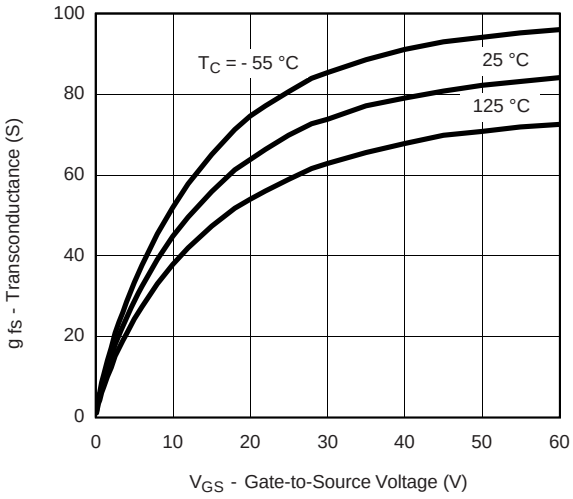
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



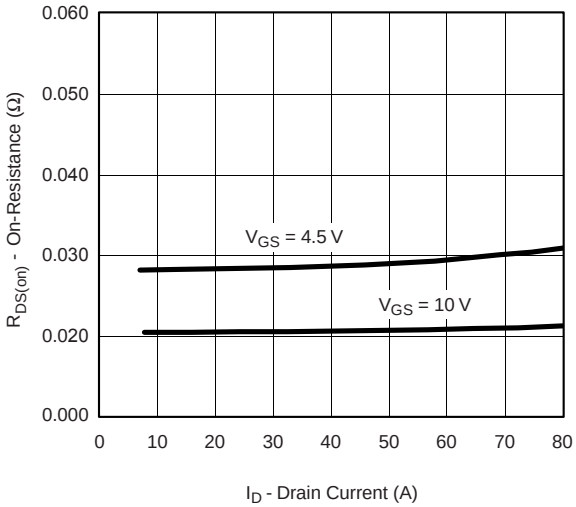
Output Characteristics



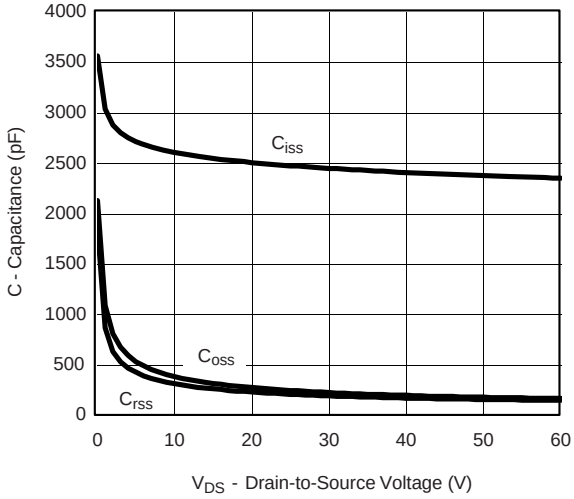
Transfer Characteristics



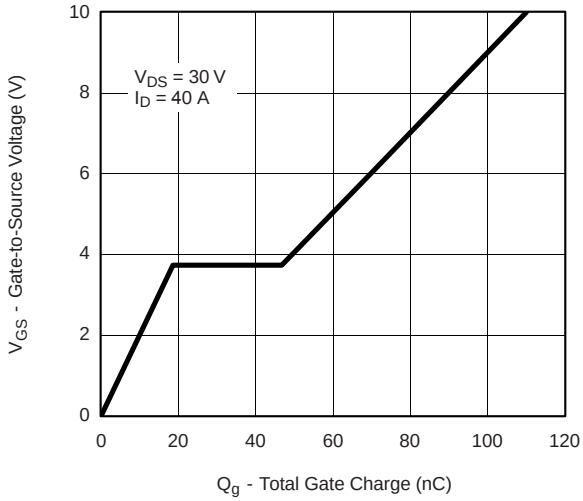
Transconductance



On-Resistance vs. Drain Current

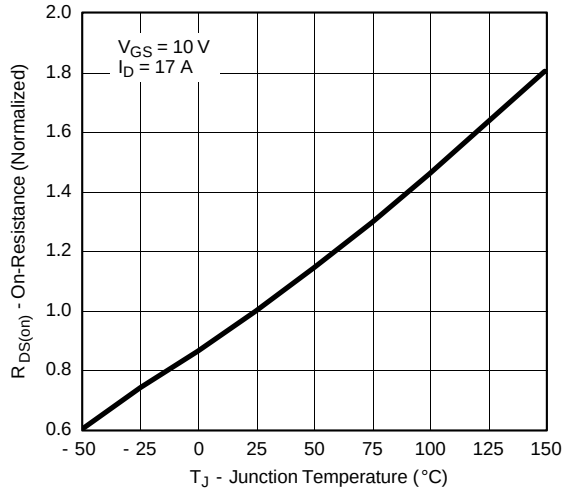


Capacitance

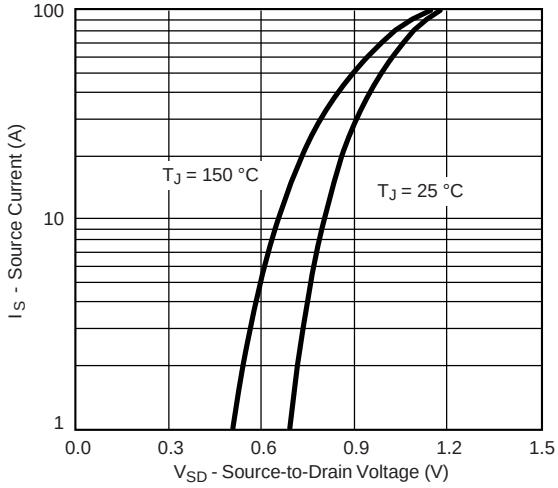


Gate Charge

TYPICAL CHARACTERISTICS

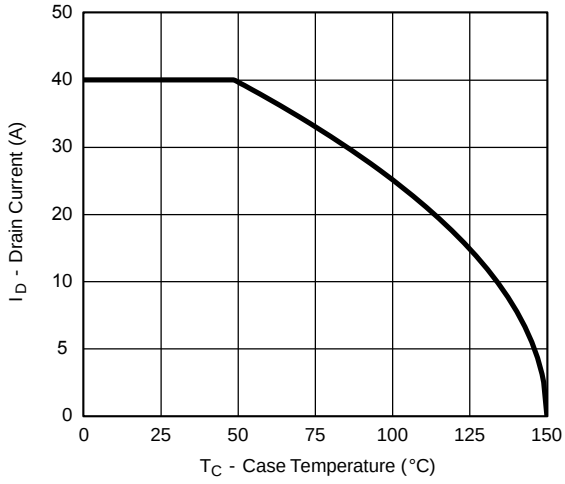


On-Resistance vs. Junction Temperature

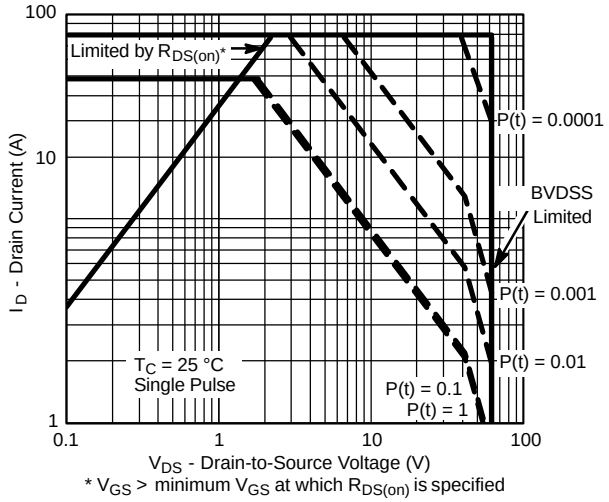


Source-Drain Diode Forward Voltage

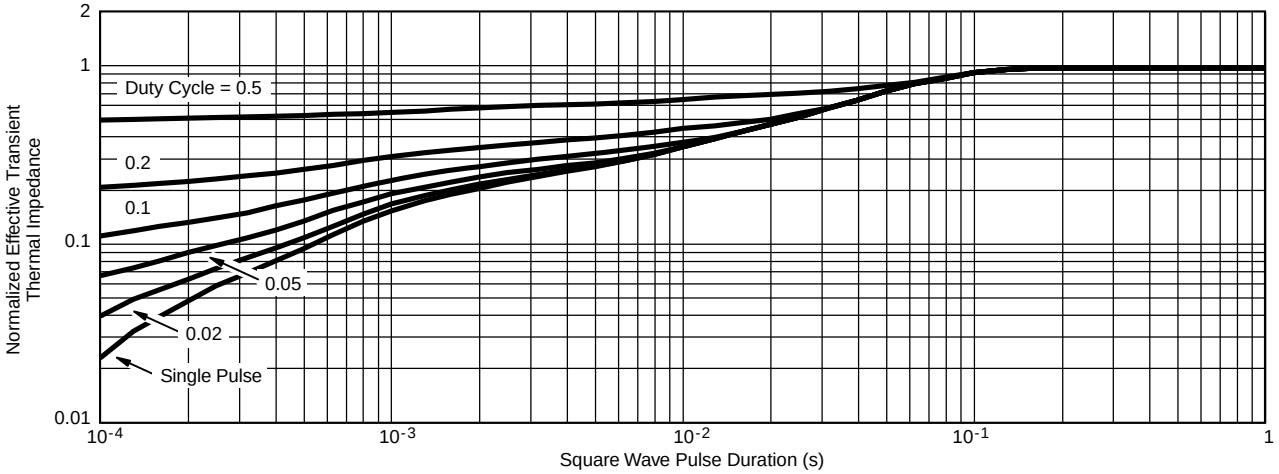
THERMAL RATINGS (25 °C, unless otherwise noted)



Drain Current vs. Case Temperature

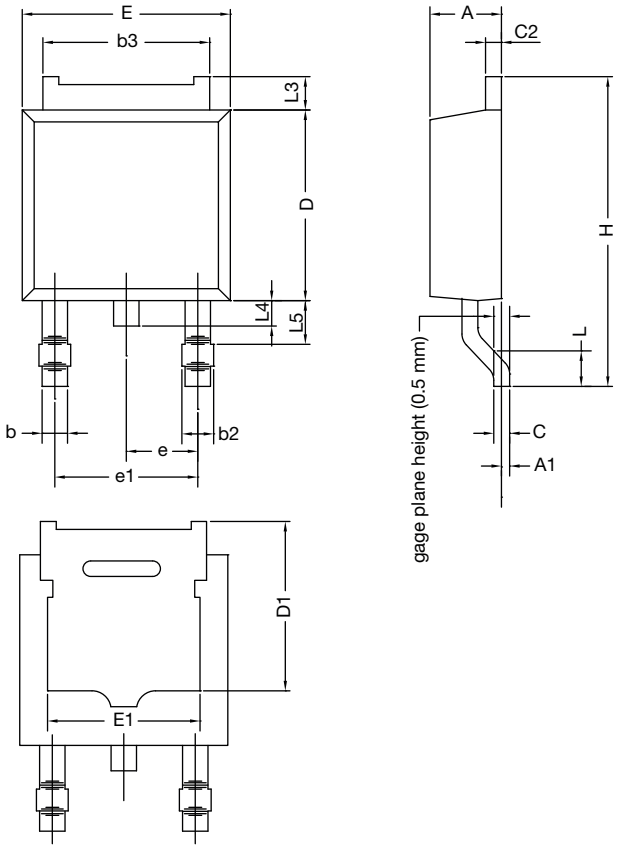


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252AA CASE OUTLINE

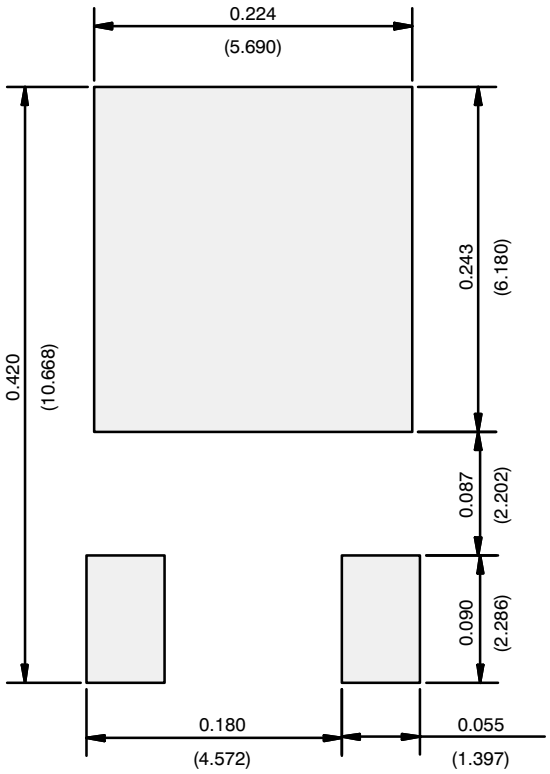


	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)